BC327, BC327-16, BC327-25, BC327-40

Amplifier Transistors

PNP Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-45	Vdc
Collector - Emitter Voltage	V _{CES}	-50	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	Ic	-800	mAdc
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	625 5.0	mW mW/°C
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

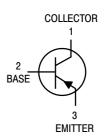
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

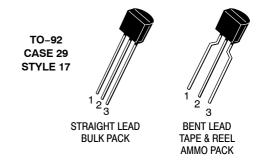
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



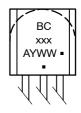
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



BCxxx = Device Code

A = Assembly Location

Y = Year WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 4 of this data sheet.

1

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BC327, BC327-16, BC327-25, BC327-40

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = -10 mA, I _B = 0)		V _{(BR)CEO}	-45	-	-	Vdc
Collector – Emitter Breakdown Voltage ($I_C = -100 \mu A, I_E = 0$)		V _{(BR)CES}	-50	_	_	Vdc
Emitter – Base Breakdown Voltage $(I_E = -10 \mu A, I_C = 0)$		V _{(BR)EBO}	-5.0	-	-	Vdc
Collector Cutoff Current (V _{CB} = -30 V, I _E = 0)		I _{CBO}	_	-	-100	nAdc
Collector Cutoff Current (V _{CE} = -45 V, V _{BE} = 0)		I _{CES}	_	-	-100	nAdc
Emitter Cutoff Current (V _{EB} = -4.0 V, I _C = 0)		I _{EBO}	_	-	-100	nAdc
ON CHARACTERISTICS						
DC Current Gain $(I_C = -100 \text{ mA}, V_{CE} = -1.0 \text{ V})$ $(I_C = -300 \text{ mA}, V_{CE} = -1.0 \text{ V})$	BC327 BC327-16 BC327-25 BC327-40	h _{FE}	100 100 160 250 40	- - - -	630 250 400 630	-
Base–Emitter On Voltage (I _C = -300 mA, V _{CE} = -1.0 V)		V _{BE(on)}	_	_	-1.2	Vdc
Collector – Emitter Saturation Voltage (I _C = -500 mA, I _B = -50 mA)		V _{CE(sat)}	_	-	-0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Output Capacitance (V _{CB} = -10 V, I _E = 0, f = 1.0 MHz)		C _{ob}	_	11	-	pF
Current – Gain – Bandwidth Product (I _C = –10 mA, V _{CE} = –5.0 V, f = 100 MHz)		f _T	_	260	_	MHz

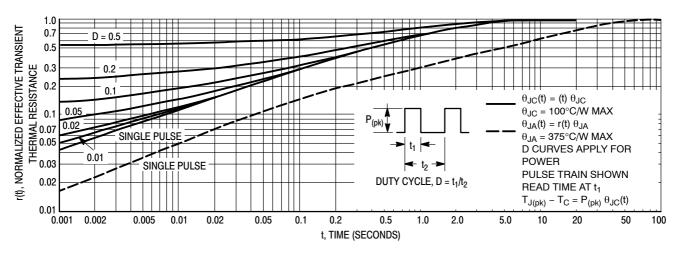
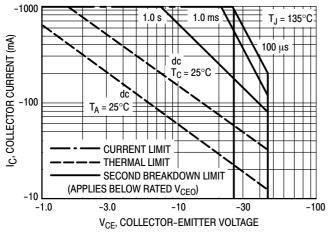


Figure 1. Thermal Response

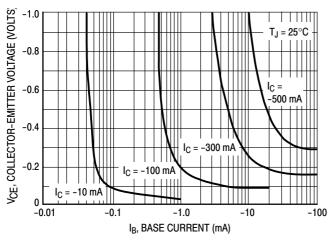
BC327, BC327-16, BC327-25, BC327-40



1000 V_{CE} = -1.0 V V

Figure 2. Active Region - Safe Operating Area

Figure 3. DC Current Gain



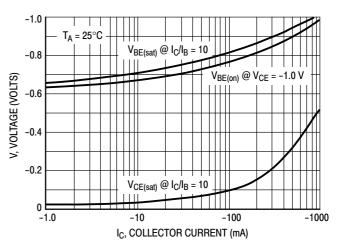
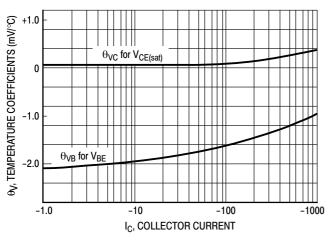


Figure 4. Saturation Region

Figure 5. "On" Voltages



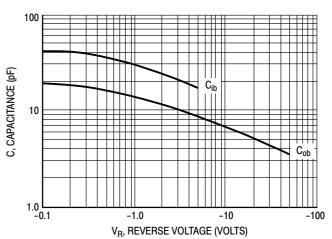


Figure 6. Temperature Coefficients

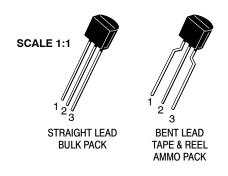
Figure 7. Capacitances

BC327, BC327-16, BC327-25, BC327-40

ORDERING INFORMATION

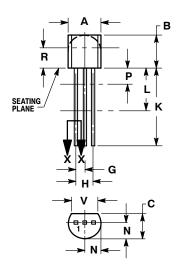
Device Order Number	Specific Device Marking	Package Type	Shipping [†]
BC327G	7	TO-92 Straight Lead (Pb-Free)	5000 Units / Bulk
BC327RL1G	327	TO-92 Bent Lead (Pb-Free)	2000 / Tape & Reel
BC327-025G	327	TO-92 Straight Lead (Pb-Free)	5000 Units / Bulk
BC327-25RL1G	7–25	TO-92 Bent Lead (Pb-Free)	2000 / Tape & Reel
BC327-25ZL1G	32725	TO-92 Bent Lead (Pb-Free)	2000 / Tape & Ammo Box
BC327-40ZL1G	7–40	TO-92 Bent Lead (Pb-Free)	2000 / Tape & Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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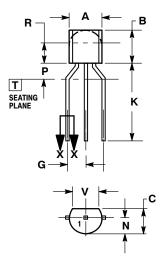


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
v	0.135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS			
DIM	MIN	MAX		
Α	4.45	5.20		
В	4.32	5.33		
С	3.18	4.19		
D	0.40	0.54		
G	2.40	2.80		
J	0.39	0.50		
K	12.70			
N	2.04	2.66		
P	1.50	4.00		
R	2.93			
V	3.43			

STYLES ON PAGE 2

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TO-92 (TO-226) CASE 29-11

ISSUE AM

DATE 09 MAR 2007

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE GATE
STYLE 11: PIN 1. 2. 3.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	PIN 1. 2.	
2.	ANODE GATE CATHODE	2.	BASE	2.	ANODE CATHODE NOT CONNECTED	2.	ANODE	2.	NOT CONNECTED
PIN 1. 2.	COLLECTOR	PIN 1. 2.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2. 3.	EMITTER COLLECTOR/ANODE CATHODE		MT 1 GATE
		2.	MT SUBSTRATE MT	2.		PIN 1. 2.	ANODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE
	GATE	PIN 1. 2.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	2.			

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